

DPS2025 Timetable (tentative)

November 13 (Thu)		November 14 (Fri)		
8:10				
8:20			Registration	
8:30	Registration			
8:40				
8:50				
9:00				
9:10				
9:20	Opening Remark / Award Ceremony			
9:30				
9:40	Nishizawa Award Lecture Masaru Izawa (Hitachi High-Tech Corporation) "Understanding Plasma Etching Processes through Surface Reaction Models"			
9:50				
10:00				
10:10	Break 10min			
10:20				
10:30	A-1 <Invited> Sung-II Cho (Samsung Electronics Co., Ltd.) "Breaking new ground : From current progress to future innovations in HARC etching technology"			
10:40				
10:50				
11:00				
11:10	A-2 <invited> Thorsten Lill (Lam Research Corporation) "Ion scattering during cryo etching of silicon oxides and nitrides"			
11:20				
11:30				
11:40				
11:50				
12:00				
12:10				
12:20	Poster Session Day1 (80min)			
12:30				
12:40				
12:50				
13:00				
13:10				
13:20				
13:30	Lunch Break 13:00-14:20 (80min)			
13:40				
13:50				
14:00				
14:10				
14:20	B-1 J. Hoang (Lam Research Corp.) "Deposition and Etch Co-Optimization for Merged 3D NAND Memory Hole and Interlayer Dielectric Contact Etches"			
14:30				
14:40	B-2 T. Kurushima (Nagoya Univ.) "Effect of Gas-Phase Radical Composition Ratio on Crx Sticking Probability in High-Aspect-Ratio Holes"			
14:50				
15:00	B-3 K. Tanaka (Daikin Industries, Ltd.) "Novel Additive Gas Development for HF-based Cryogenic HAR Dielectric Etching using Digital Twin"			
15:10				
15:20				
15:30	Break 20min			
15:40				
15:50	C-1 M. Sekine (Nagoya Univ.) "Role of H2O in SiO2 cryogenic etching using HF plasma"			
16:00				
16:10	C-2 T. Imamura (Hitachi, Ltd.) "Depth control of protection layer for HF gas etching via TMSDMA vapor exposure"			
16:20	D-1 D. Kim (Nagoya Univ.) "Quantitative evaluation of the influence of ion-neutral collisions in the sheath on ion angular distributions"			
16:30				
16:40				
16:50	Break 20min			
17:00				
17:10	E-1 <invited> Vincent M. Donnelly (University of Houston) "Mechanistic Insights and New Approaches to Atomic Layer Etching of Silicon in Chlorine and Bromine-Containing Plasmas"			
17:20				
17:30				
17:40	E-2 M. Fukasawa (AIST) "Plasma-surface interactions of extreme ultraviolet photoresist in atomic layer etching processes"			
17:50				
18:00	E-3 M. ADJABI (Univ. of Orleans) "Cryogenic Atomic Layer Etching of MoS2 using Cyclic Fluorocarbon and Argon plasma"			
18:10				
18:20	E-4 L. Ghorbani (Ku Leuven and imec) "ALE and Pulsed ALE of Mg-based Oxide Semiconductors (MgZnO) at Sub-100 nm Pitches Using Ru Hard Mask"			
18:30				
18:40				
18:50				
19:00				
19:10				
19:20				
19:30				
19:40				
19:50				
20:00	Banquet			
20:10				
20:20				
20:30				
20:40				
20:50				
21:00				

Session F
AS2. Atomic layer processes (ALE/ALD/ASD) for ultimate control of surface reaction

Session G
Computational Approaches (Modeling, Simulation, Machine Learning, AI, Informatics, DX) for Dry Process

Session H
AS3. Dry process technology for 3D-IC and advanced packaging

Session I
New Dry Process Concepts

Session J
Surface Reaction and Damage

Session K
Deposition Technologies (CVD / PVD)